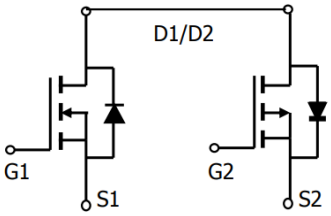
AP20G06GD

60V N+P-Channel Enhancement Mode MOSFET

Description

The AP20G06GD uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



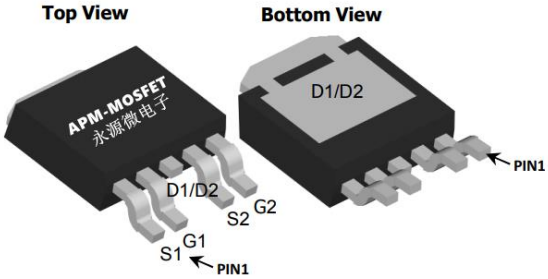
General Features

V_{DS} = 60V I_D =25A

$R_{DS(ON)}$ < 40mΩ @ V_{GS}=10V （Type：32mΩ）

V_{DS} = -60V I_D =-19A

$R_{DS(ON)}$ < 90mΩ @ V_{GS}=-10V （Type：70mΩ）



Application

Boost driver

Brushless motor

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP20G06GD	TO-252-4L	AP20G06GD XXX YYYY	2500

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating		Units
		N-Channel	P-Channel	
VDS	Drain-Source Voltage	60	-60	V
VGS	Gate-Source Voltage	±20	±20	V
ID@TC=25℃	Continuous Drain Current, VGS @ 10V1	25	-19	A
ID@TC=100℃	Continuous Drain Current, VGS @ 10V1	14	-8.5	A
IDM	Pulsed Drain Current2	60	-30	A
EAS	Single Pulse Avalanche Energy3	22	29.8	mJ
IAS	Avalanche Current	21	-19	A
PD@TC=25℃	Total Power Dissipation4	50	50	W
TSTG	Storage Temperature Range	-55 to 175	-55 to 175	℃
TJ	Operating Junction Temperature Range	-55 to 175	-55 to 175	℃
RθJA	Thermal Resistance Junction-Ambient 1	62		℃/W
RθJC	Thermal Resistance Junction-Case1	3		℃/W

N-Channel Electrical Characteristics (TJ =25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	60	65	---	V
△BVDSS/△TJ	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.063	---	V/℃
RDS(ON)	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=5A	---	32	40	mΩ
		V_{GS}=4.5V , I_D=4A	---	48	60	
VGS(th)	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	1.75	2.5	V
△$V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.24	---	mV/℃
IDSS	Drain-Source Leakage Current	V_{DS}=48V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=48V , V_{GS}=0V , T_J=55℃	---	---	5	
IGSS	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=4A	---	28	---	S
Q_g	Total Gate Charge (4.5V)	V_{DS}=48V , V_{GS}=4.5V , I_D=4A	---	19	---	nC
Qgs	Gate-Source Charge		---	2.6	---	
Qgd	Gate-Drain Charge		---	4.1	---	
Td(on)	Turn-On Delay Time	V_{DD}=30V , V_{GS}=10V , R_G=3.3Ω, I_D=4A	---	3	---	ns
T_r	Rise Time		---	34	---	
Td(off)	Turn-Off Delay Time		---	23	---	
T_f	Fall Time		---	6.0	---	
Ciss	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	1027	---	pF
Coss	Output Capacitance		---	65	---	
Crss	Reverse Transfer Capacitance		---	45	---	
IS	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	2.5	A
VSD	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V

Note :

1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3、The EAS data shows Max. rating . The test condition is V DD =25V,V GS =10V,L=0.1mH,IAS =21A

4、The power dissipation is limited by 150℃ junction temperature

5、The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation

P-Channel Electrical Characteristics (TJ =25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-60	-65	---	V
△BVDSS/△TJ	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.03	---	V/℃
RDS(ON)	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-3A	---	70	90	mΩ
		V_{GS}=-4.5V , I_D=-2A	---	88	100	
VGS(th)	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.2	1.75	-2.5	V
IDSS	Drain-Source Leakage Current	V_{DS}=-48V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=-48V , V_{GS}=0V , T_J=55℃	---	---	5	
IGSS	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-3A	---	8.5	---	S
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-48V , V_{GS}=-4.5V , I_D=-3A	---	12.1	---	nC
Qgs	Gate-Source Charge		---	2.2	---	
Qgd	Gate-Drain Charge		---	6.3	---	
Td(on)	Turn-On Delay Time	V_{DD}=-15V , V_{GS}=-10V , R_G=3.3Ω, I_D=-1A	---	9.2	---	ns
T_r	Rise Time		---	20.1	---	
Td(off)	Turn-Off Delay Time		---	46.7	---	
T_f	Fall Time		---	9.4	---	
Ciss	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	1137	---	pF
Coss	Output Capacitance		---	76	---	
Crss	Reverse Transfer Capacitance		---	50	---	
IS	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	-2.5	A
VSD	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.2	V

Note :

1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3、The EAS data shows Max. rating . The test condition is V DD =-25V,V GS =-10V,L=0.1mH,IAS =-19A

4、The power dissipation is limited by 150℃ junction temperature

5、The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

N-Channel Typical Characteristics

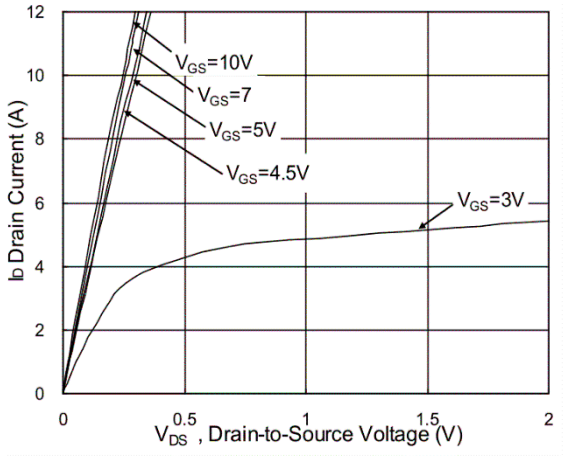


Fig.1 Typical Output Characteristics

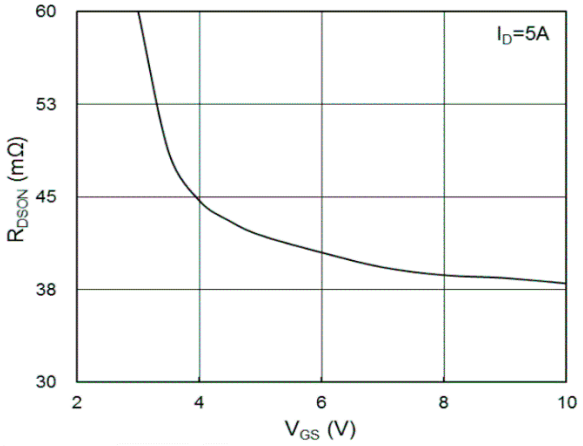


Fig.2 On-Resistance vs. G-S Voltage

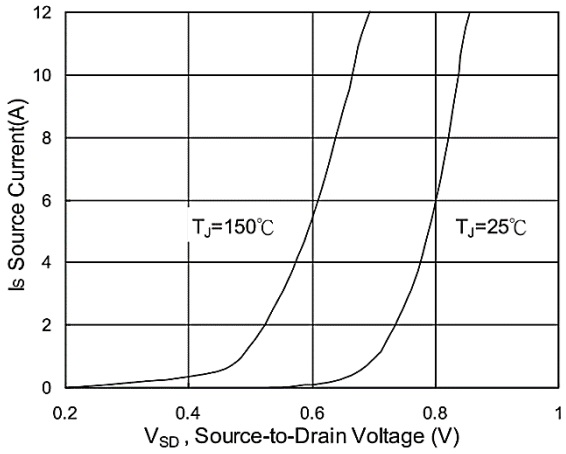


Fig.3 Source Drain Forward Characteristics

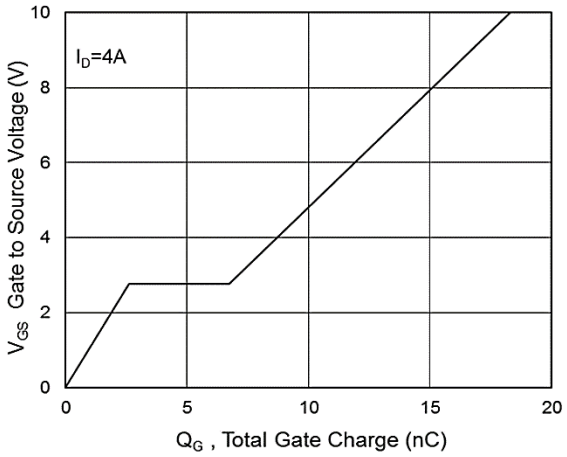


Fig.4 Gate-Charge Characteristics

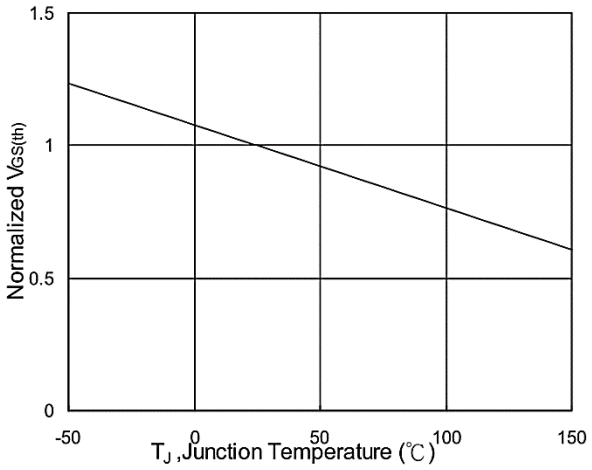


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

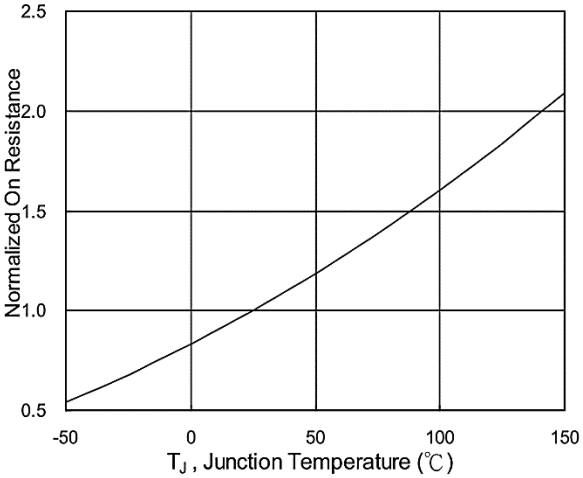


Fig.6 Normalized R_{DSON} vs. T_J

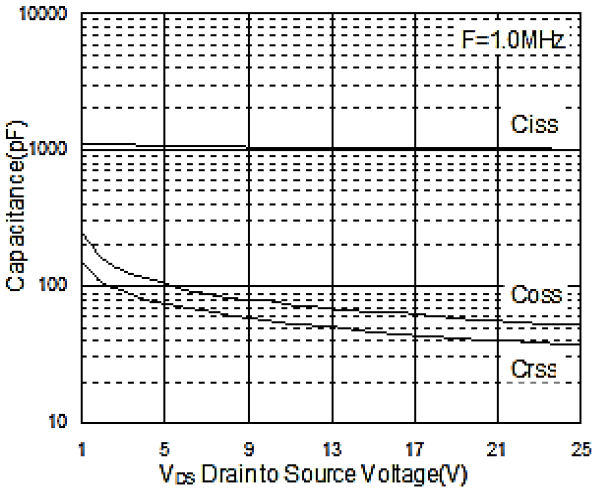


Fig.7 Capacitance

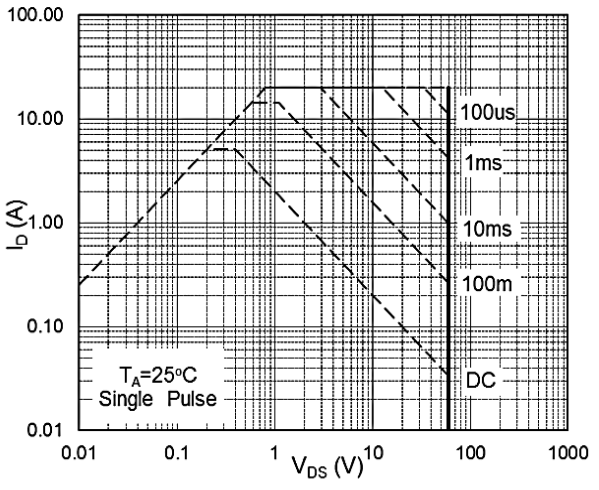


Fig.8 Safe Operating Area

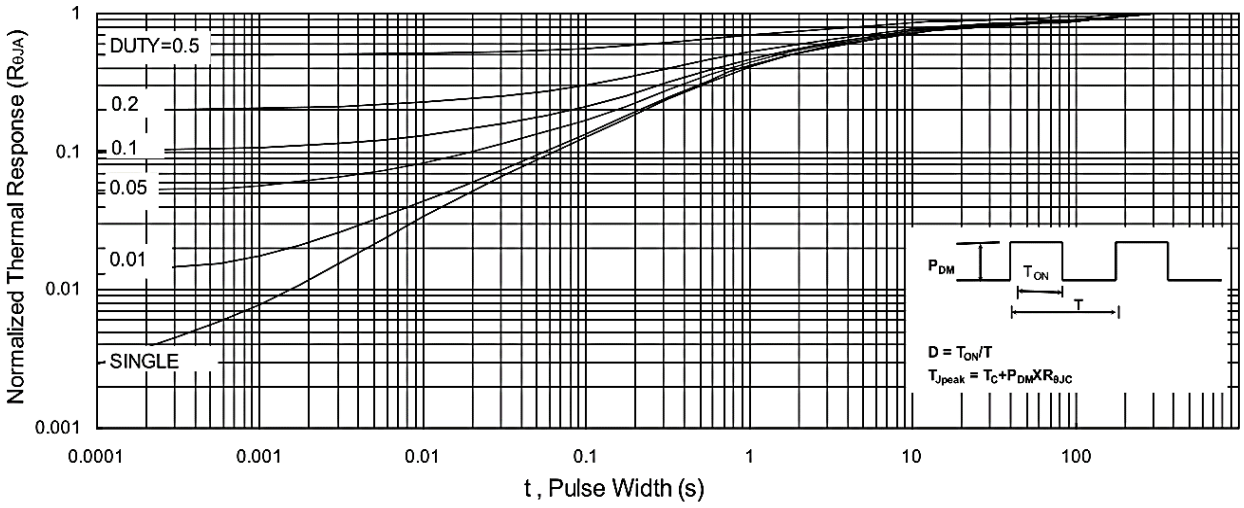


Fig.9 Normalized Maximum Transient Thermal Impedance

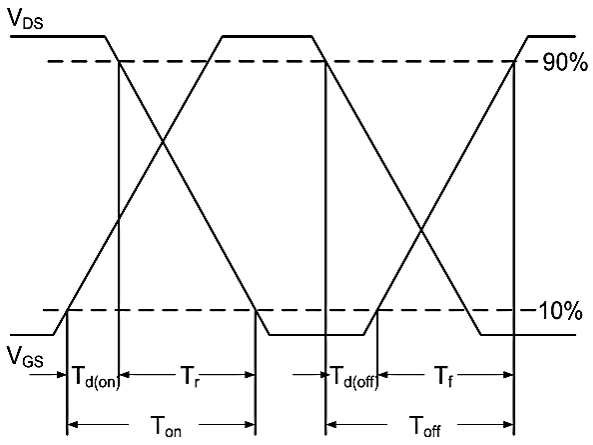


Fig.10 Switching Time Waveform

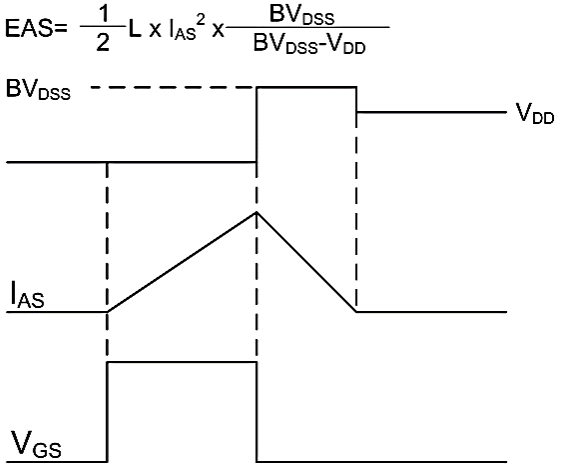


Fig.11 Unclamped Inductive Waveform

P-Channel Typical Characteristics

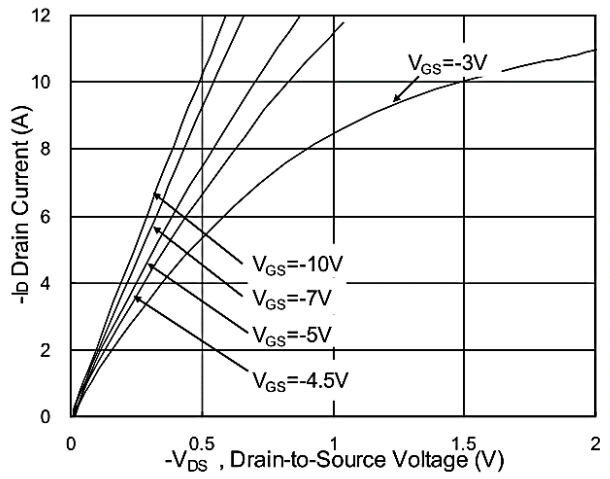
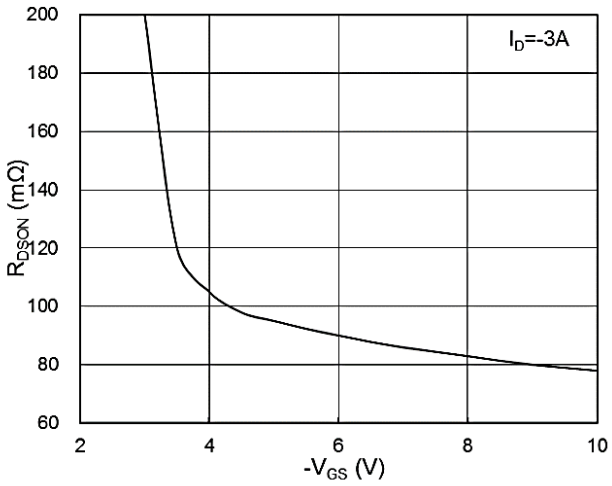


Fig.1 Typical Output Characteristics



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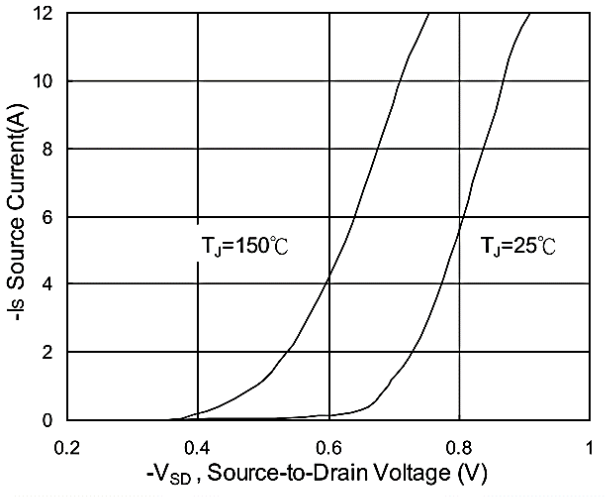
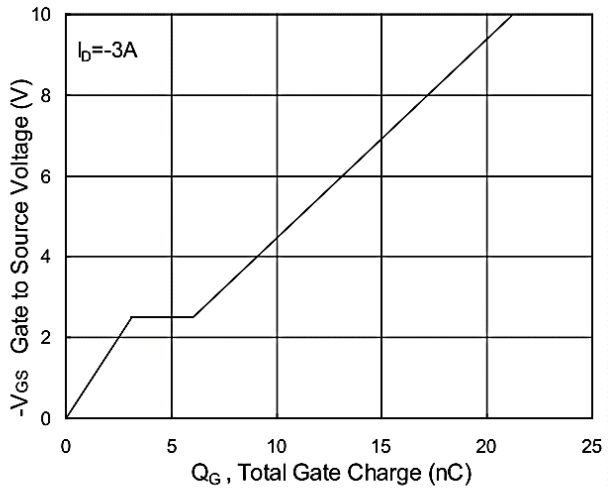


Fig.3 Source Drain Forward Characteristics



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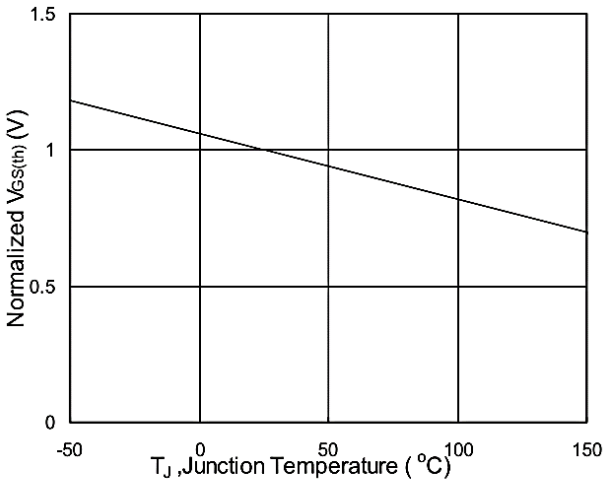

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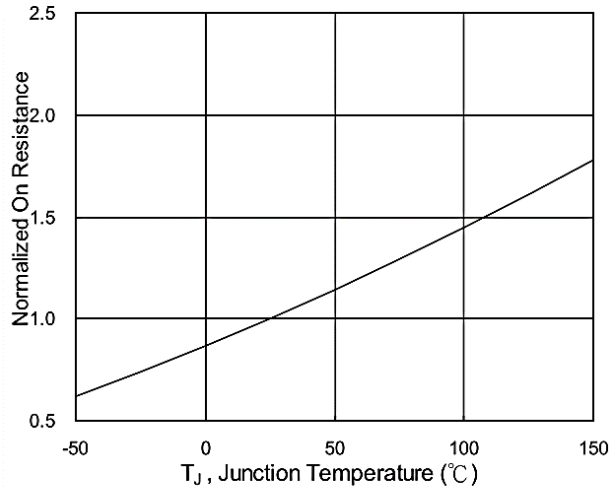


Fig.6 Normalized R_{DSON} vs. T_J

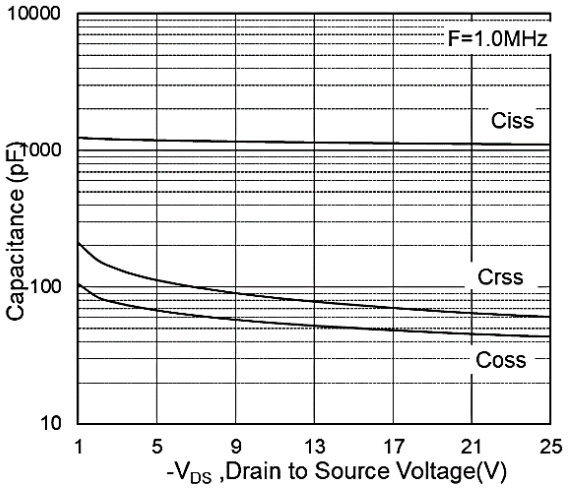


Fig.7 Capacitance

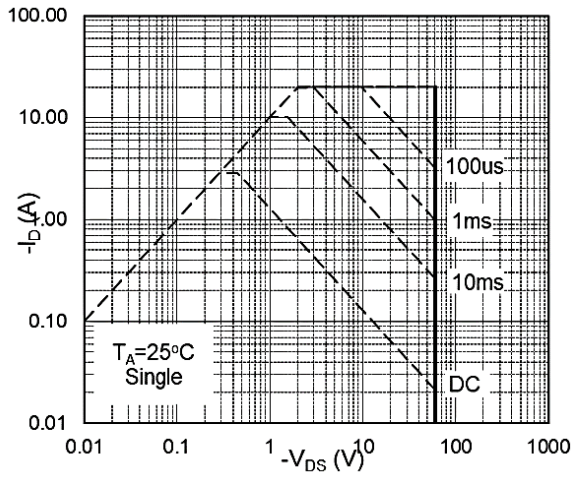
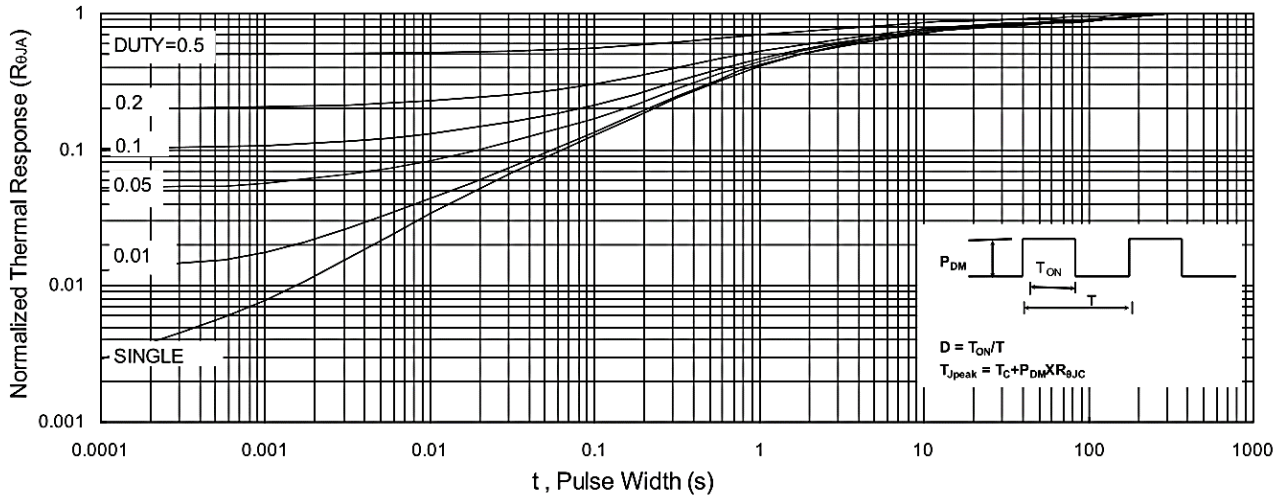


Fig.8 Safe Operating Area



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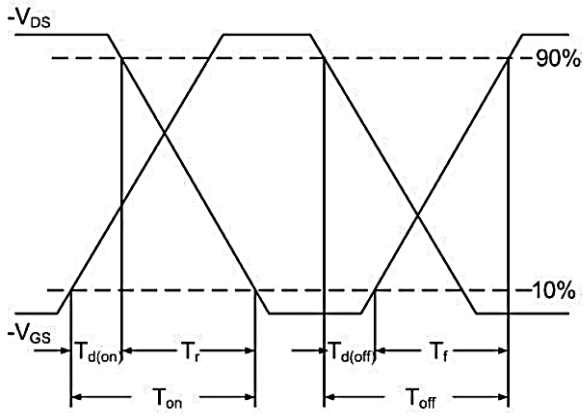


Fig.10 Switching Time Waveform

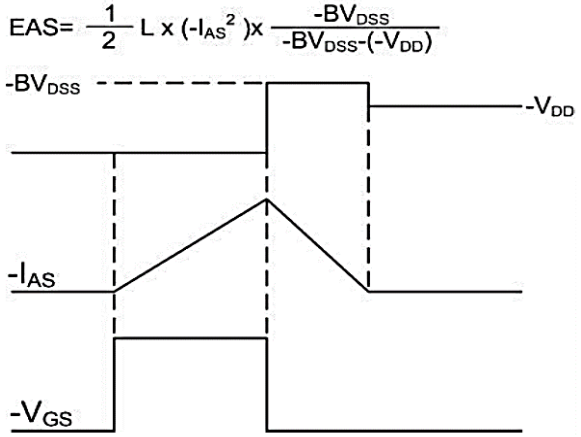
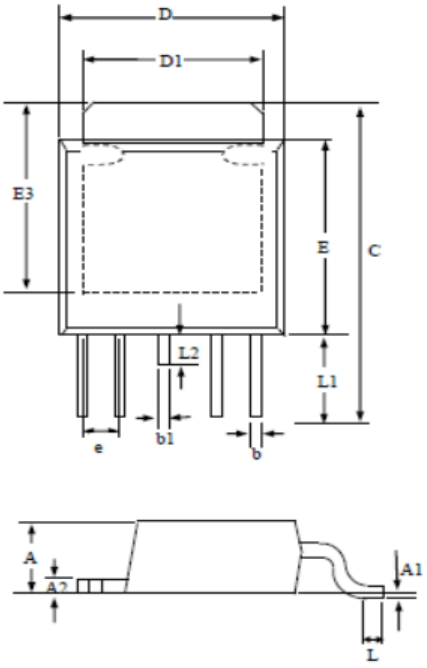


Fig.11 Unclamped Inductive Waveform

60V N+P-Channel Enhancement Mode MOSFET

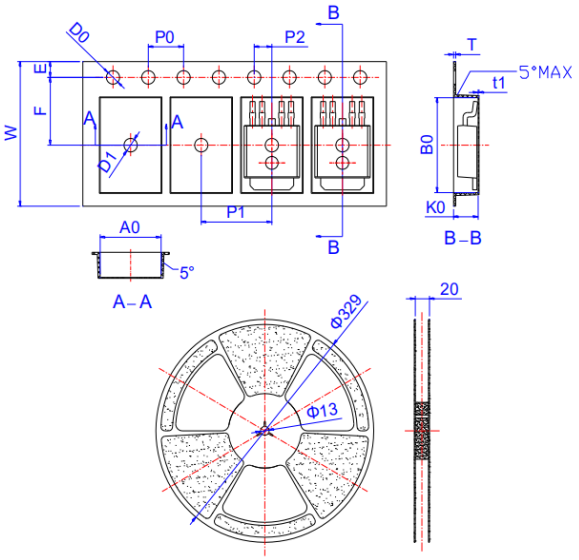
Package Mechanical Data:TO-252-4L



SYMBOLS	Millimeters		
	MIN	NOM	MAX
D	6.30	6.55	6.80
D1	4.80	5.35	5.90
C	9.30	9.75	10.20
E	5.30	5.80	6.30
E3	4.50	5.15	5.80
L	0.90	1.35	1.80
L1	2.00	2.53	3.05
L2	0.50	0.85	1.20
b	0.30	0.50	0.70
b1	0.40	0.60	0.80
A	2.10	2.30	2.50
A2	0.40	0.53	0.65
A1	0.00	0.10	0.20
e	1.20	1.30	1.40

1.All Dimensions Are in Millimeters.
2.Dimension Does Not Include Mold Protrusions.

Reel Specification-TO-252-4



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

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Edition	Date	Change
Rve1.0	2021/5/31	Initial release